

**IN THE CLAIMS**

*Please amend the claims as follows:*

1. (Currently Amended) A semiconductor laser device, comprising:  
a semiconductor laser element arranged inside an airtight-sealed package, the semiconductor laser element having an active region ~~made of one material selected from the group consisting of an AlGaAs-based crystal, an AlGaInP-based crystal, an AlGaN-based crystal, and an InGaN-based crystal~~ formed of a gallium nitride-based crystal,  
wherein an atmospheric gas inside the package contains oxygen.
2. (Original) The semiconductor laser device of claim 1, wherein the semiconductor laser element has a dielectric oxide film formed on a laser emission surface thereof.
3. (Currently Amended) The semiconductor laser device of claim 1, wherein a rated output of the semiconductor laser device is 30 mW or more, and  
the atmospheric gas inside the package is a mixture of oxygen and nitrogen, with an oxygen content of 20% or more.
4. (Original) The semiconductor laser device of claim 1, wherein the semiconductor laser element emits light having a wavelength of 0.9  $\mu\text{m}$  or less.
5. (Currently Amended) ~~A~~ The semiconductor laser device comprising a semiconductor laser element arranged inside an airtight-sealed package of claim 1, wherein the semiconductor

laser element operating at a rated output power of the semiconductor laser device is 30 mW or more, wherein an

the atmospheric gas inside the package contains oxygen is dry air.

6. (Cancelled)

7. (Cancelled)

8. (Cancelled)

9. (New) The semiconductor laser device of claim 1, wherein the gallium nitride-based crystal is an AlGaN- or InGaN-based crystal.